



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C		
60V	$12m\Omega @V_{GS} = 10V$	37.2A		
	$14.5 \text{m}\Omega @V_{GS} = 4.5 \text{V}$	33.9A		

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- **DC-DC Converters**
- **Power Management Functions**
- Load Switch

Features

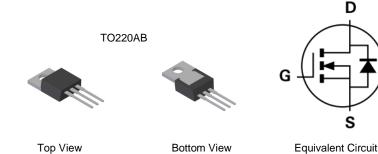
- Excellent QGD x RDS(ON) Product (FOM)
- Advanced Technology for DC-DC Converts
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

Case: TO220AB

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- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



Top View Pin-Out Configuration

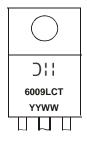
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6009LCT	TO220AB	50 Pieces/Tube

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain < 900ppm bromine, < 900ppm chlorine (< 1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



☐ ☐ Manufacturer's Marking 6009LCT = Product Type Marking Code YYWW = Date Code Marking YY or YY = Last Digit of Year (ex: 16 = 2016) WW or <u>WW</u> = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±16	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	37.2 29.8	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Maximum Body Diode Forward Current (Note 6)	I _S	80	Α	
Avalanche Current, L = 0.1mH	I _{AS}	19.8	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	19.6	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	55	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P _D	25	W
Thermal Resistance, Junction to Case (Note 6)		ReJC	5	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

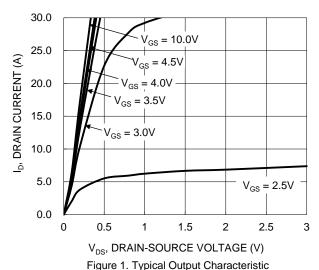
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV_{DSS}	60			V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.7	1	2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			9.4	12	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	_	7.6	14.5	11177	$V_{GS} = 4.5V, I_D = 11.5A$	
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{ISS}	_	1,925	_		$V_{DS} = 30V$, $f = 1MHz$, $V_{GS} = 0V$	
Output Capacitance	Coss	_	438	_	pF		
Reverse Transfer Capacitance	C _{RSS}	_	41	_			
Gate Resistance	R_{G}	_	1.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	15.6	_		V _{DD} = 30V, I _D = 13.5A	
Total Gate Charge (V _{GS} = 10V)	Q_{G}		33.5		nC		
Gate-Source Charge	Q _{GS}	_	4.7	_	no		
Gate-Drain Charge	Q_{GD}	_	5.3	_			
Turn-On Delay Time	t _{D(ON)}		4.5	_		V _{DS} = 30V, V _{GS} = 10V,	
Turn-On Rise Time	t _R		8.6	_	20		
Turn-Off Delay Time	t _{D(OFF)}		35.9	_	ns	$R_G = 6\Omega$, $I_D = 13.5A$	
Turn-Off Fall Time	t _F	_	15.7	_			
Reverse Recovery Time	t _{RR}		18.2	_	ns	10.50 4:/4+ 1000//	
Reverse Recovery Charge	Q_{RR}	_	33.1	_	nC	$I_F = 13.5A$, di/dt = 100A/ μ s	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- Device mounted on an infinite heat sink.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





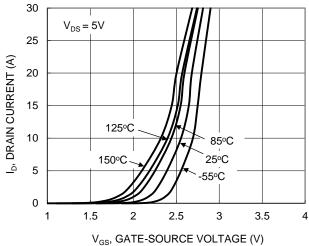


Figure 2. Typical Transfer Characteristic

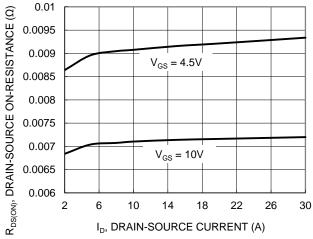
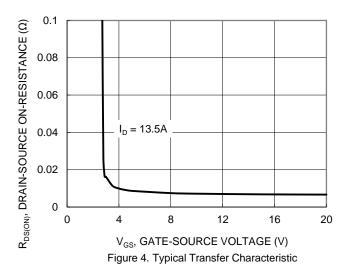


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



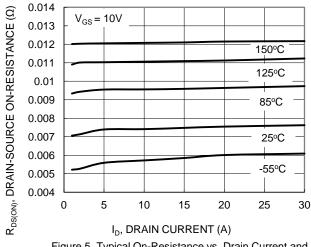


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

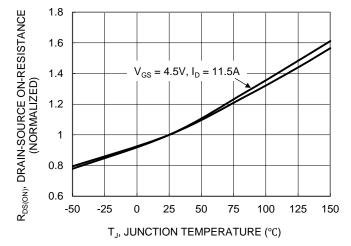


Figure 6. On-Resistance Variation with Junction Temperature



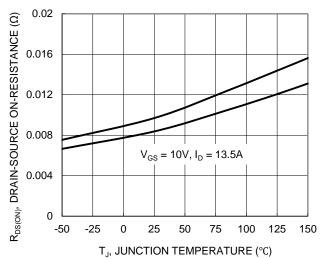


Figure 7. On-Resistance Variation with Junction Temperature

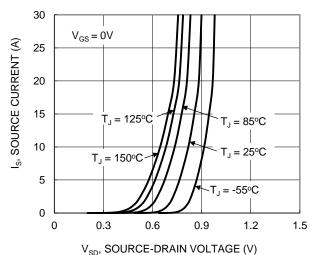


Figure 9. Diode Forward Voltage vs. Current

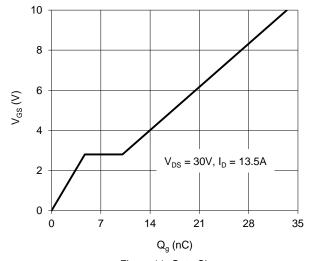


Figure 11. Gate Charge

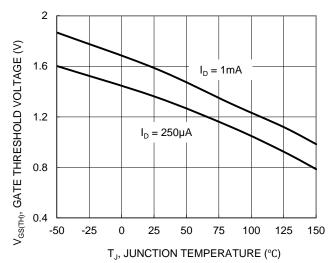


Figure 8. Gate Threshold Variation vs. Junction Temperature

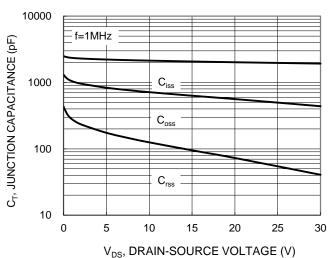


Figure 10. Typical Junction Capacitance

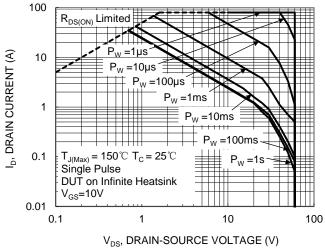


Figure 12. SOA, Safe Operation Area



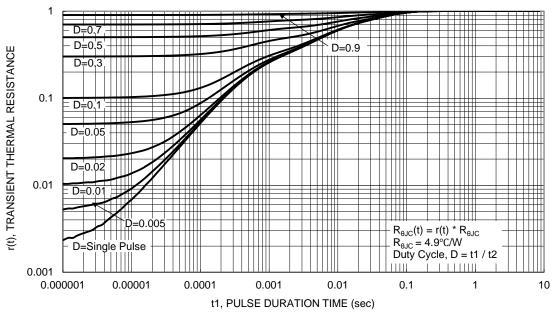


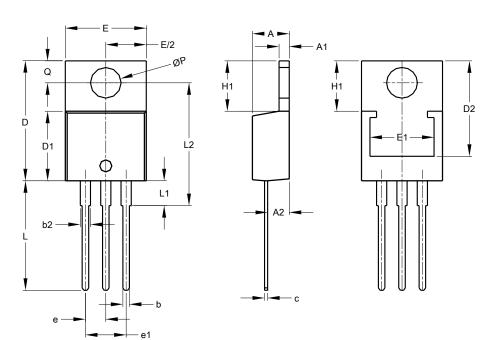
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



TO220AB					
Dim	Min	Max	Тур		
Α	3.56	4.82	1		
A1	0.51	1.39	ı		
A2	2.04	2.92	_		
b	0.39	1.01	0.81		
b2	1.15	1.77	1.24		
С	0.356	0.61	1		
D	14.22	16.51	ı		
D1	8.39	9.01	1		
D2	11.45	12.87	-		
е	-	1	2.54		
e1	-	1	5.08		
Е	9.66	10.66	1		
E1	6.86	8.89	-		
H1	5.85	6.85	ı		
L	12.70	14.73	1		
L1	-	6.35	-		
L2	15.80	16.20	16.00		
Р	3.54	4.08	ı		
q	2.54	3.42	_		
All Dimensions in mm					



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